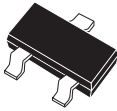


CMPT2222A

NPN SILICON TRANSISTOR



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT2222A type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications.

Marking Code is C1P.

MAXIMUM RATINGS (T_A=25°C)

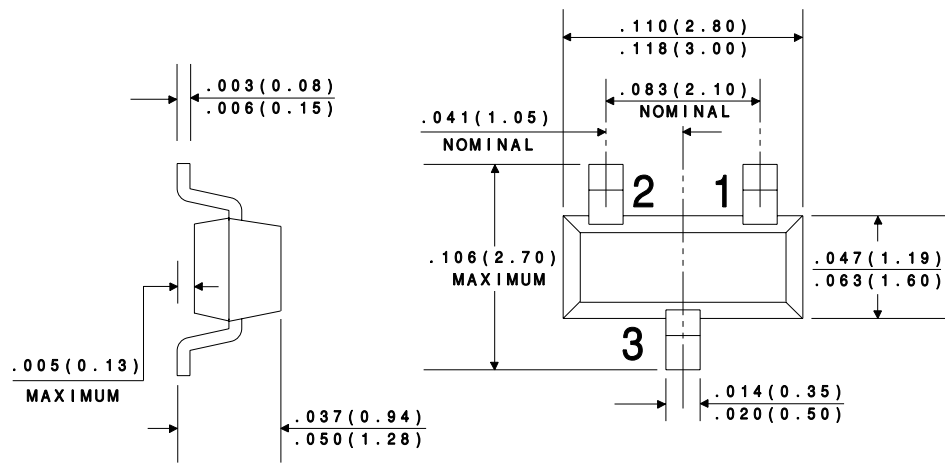
	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	600	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =60V		10	nA
I _{CBO}	V _{CB} =60V, T _A =125°C		10	μA
I _{CEV}	V _{CE} =60V, V _{EB} =3.0V		10	nA
I _{EBO}	V _{EB} =3.0V		10	nA
BV _{CBO}	I _C =10μA	75		V
BV _{CEO}	I _C =10mA	40		V
BV _{EBO}	I _E =10μA	6.0		V
V _{CE} (SAT)	I _C =150mA, I _B =15mA		0.3	V
V _{CE} (SAT)	I _C =500mA, I _B =50mA		1.0	V
V _{BE} (SAT)	I _C =150mA, I _B =15mA	0.6	1.2	V
V _{BE} (SAT)	I _C =500mA, I _B =50mA		2.0	V
h _{FE}	V _{CE} =10V, I _C =0.1mA	35		
h _{FE}	V _{CE} =10V, I _C =1.0mA	50		
h _{FE}	V _{CE} =10V, I _C =10mA	75		
h _{FE}	V _{CE} =1.0V, I _C =150mA	50		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=10V, I_C=150mA$	100	300	
h_{FE}	$V_{CE}=10V, I_C=500mA$	40		
f_T	$V_{CE}=20V, I_C=20mA, f=100MHz$	300		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0MHz$		25	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	2.0	8.0	$k\Omega$
h_{ie}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	0.25	1.25	$k\Omega$
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$		8.0	$\times 10^{-4}$
h_{re}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$		4.0	$\times 10^{-4}$
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	50	300	
h_{fe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	75	375	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	5.0	35	$\mu mhos$
h_{oe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	25	200	$\mu mhos$
$rb'C_C$	$V_{CB}=10V, I_E=20mA, f=31.8MHz$		150	ps
NF	$V_{CE}=10V, I_C=100\mu A, R_S=1.0k\Omega, f=1.0kHz$		4.0	dB
t_d	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		10	ns
t_r	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		25	ns
t_s	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		225	ns
t_f	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		60	ns

All dimensions in inches (mm).



LEAD CODE:
1) BASE
2) EMITTER
3) COLLECTOR